

**IGNITION CONDITIONS FOR PERIPHERAL PLASMA
IN A GROUNDED CHAMBER CONNECTED TO
A DUAL FREQUENCY CAPACITIVE DISCHARGE**

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Sangsup Jeong (Samsung, visiting) — experiments and modeling

Sungjin Kim — global modeling and experiments

Alan Wu — PIC simulations of heating and ion energies

Acknowledgements:

Lam Research Corporation

National Science Foundation

UC Discovery/MICRO Programs

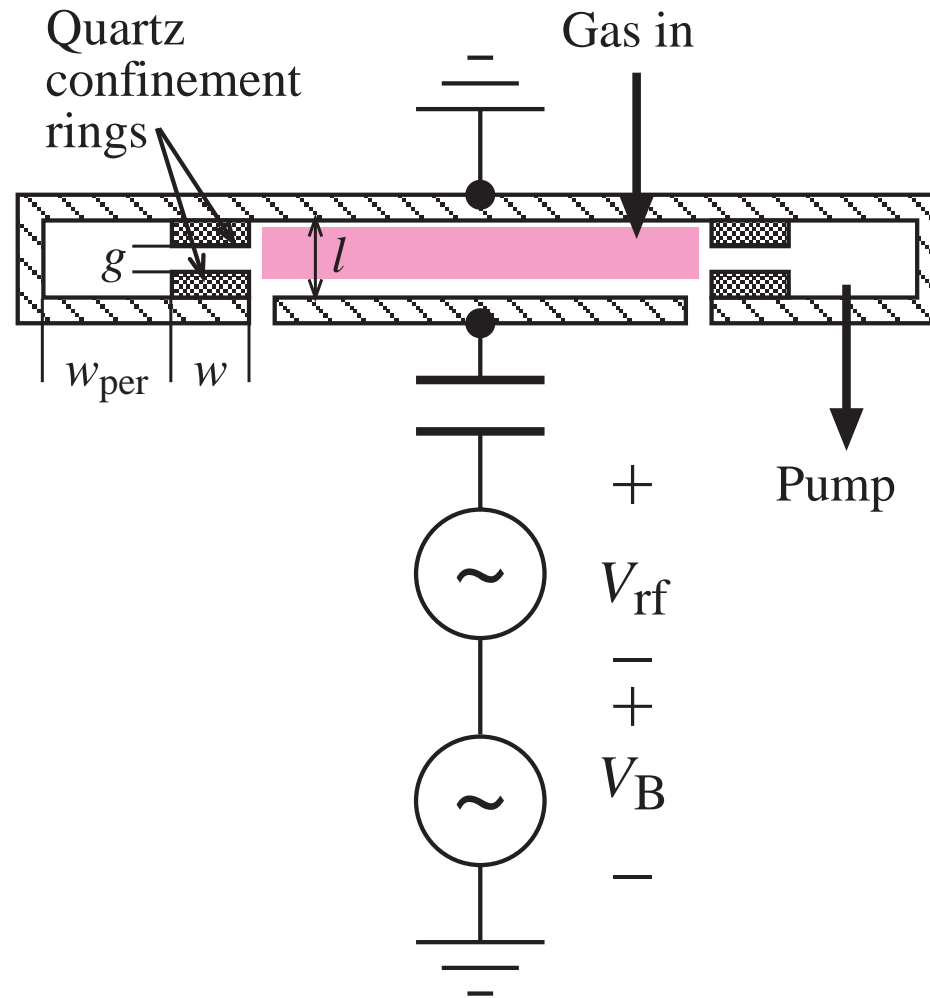
Thanks to: Doug Keil, Eric Hudson, and Reza Sadjadi

OUTLINE OF TALK

- Introduction
- Discharge confinement
 - Plasma diffusion into slot (completed)
 - Plasma maintenance in slot and periphery (main topic)
 - Berkeley experiment (in progress)

INTRODUCTION

PLASMA CONFINEMENT BY DIELECTRIC RINGS



DUAL FREQUENCY CAPACITIVE DISCHARGES

- $R \sim 15\text{--}30$ cm, $l \sim 1\text{--}3$ cm
- $p \sim 30\text{--}300$ mTorr, $\text{C}_4\text{F}_8/\text{O}_2/\text{Ar}$ feedstock
- High frequency $f_{\text{rf}} \sim 27.1\text{--}160$ MHz, $V_{\text{rf}} \sim 100\text{--}1000$ V
- Low frequency $f_B \sim 2\text{--}13.56$ MHz, $V_B \sim 500\text{--}3000$ V
- Absorbed powers P_{rf} , $P_B \sim 500\text{--}3000$ W

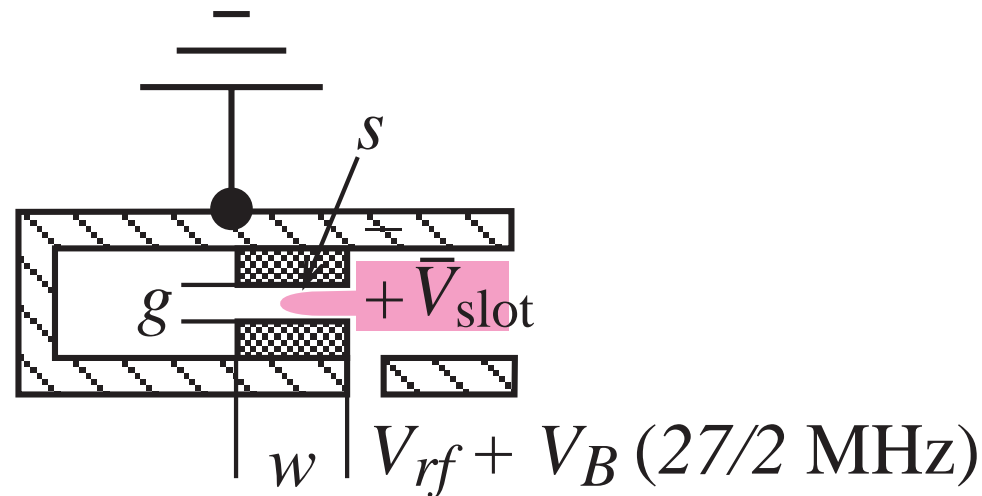
- For independent control of ion flux and energy

$$\frac{\omega_{\text{rf}}^2}{\omega_B^2} \gg \frac{V_B}{V_{\text{rf}}} \gg 1$$

(M.A. Lieberman, Jisoo Kim, J-P Booth, J-M Rax and M.M. Turner, SEMICON Korea Etching Symposium, p. 23, 2003)

PLASMA TRANSPORT THROUGH SLOT

BASIC DIFFUSION MODEL



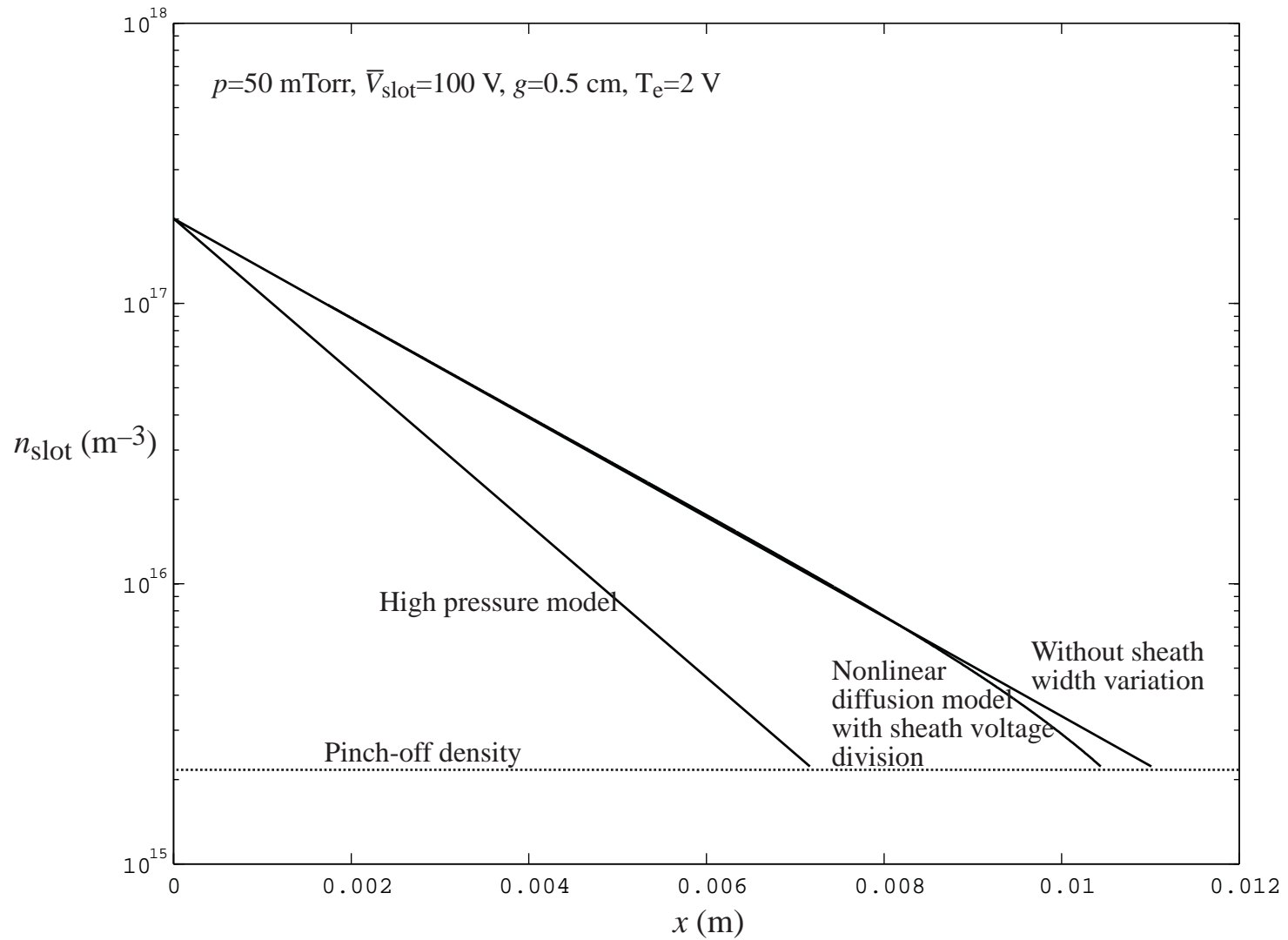
- $V_{\text{rf}} \Rightarrow$ plasma density n_0 at slot entrance
 n_{slot} decays as plasma diffuses into slot
- $V_B + V_{\text{rf}} \Rightarrow$ dc plasma potential \bar{V}_{slot} within slot
- Child law \Rightarrow sheath width s within slot
- As n_{slot} decays, s increases until $s = g/2 \Rightarrow$ plasma “pinch-off”
- Pinch-off length $x_{\text{po}} \sim 0.5\text{--}1 \text{ cm}$ for 0.5 cm gap g

IMPROVEMENTS TO MODEL

- The sheath and the quartz ring form a capacitive voltage divider for the slot voltage
⇒ reduced sheath voltage and modest increase in pinch-off length
- Low pressure diffusion model in slot for $\lambda_i \gtrsim (T_i/T_e)g$
⇒ modest increase in pinch-off length
- Sheath width varies with position within the slot
⇒ slightly reduced pinch-off length
- Finite ionization rate within the slot
⇒ modest increase in pinch-off length
- Collisional (not collisionless) Child law sheath in the slot
⇒ slightly increased pinch-off length

MODEL RESULTS

(collisionless sheath without ionization in slot)



PINCH-OFF LENGTH

- A good estimate of the pinch-off length is

$$x_{\text{po}} \sim \frac{2g}{\pi} \ln \left(0.12 \frac{g^2}{\lambda_{\text{D0}}^2} \frac{T_e^{3/2}}{\bar{V}_{\text{slot}}^{3/2}} \right)$$

where $\lambda_{\text{D0}} = (\epsilon_0 T_e / e n_o)^{1/2} =$ Debye length at slot entrance

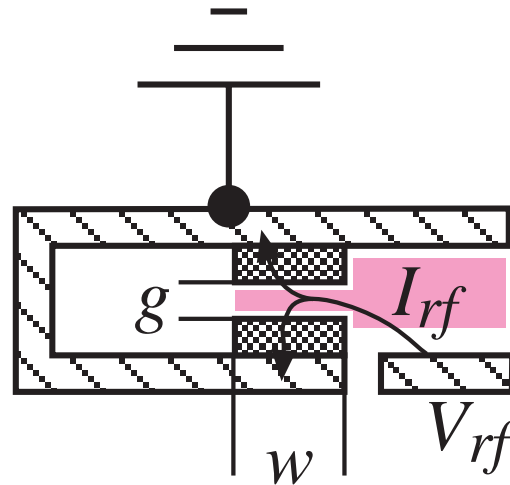
- There is a weak pressure dependence at high pressures
- For typical plasma parameters

$$x_{\text{po}} \sim 2g < \text{slot width } w$$

\Rightarrow plasma does not diffuse through slot into periphery

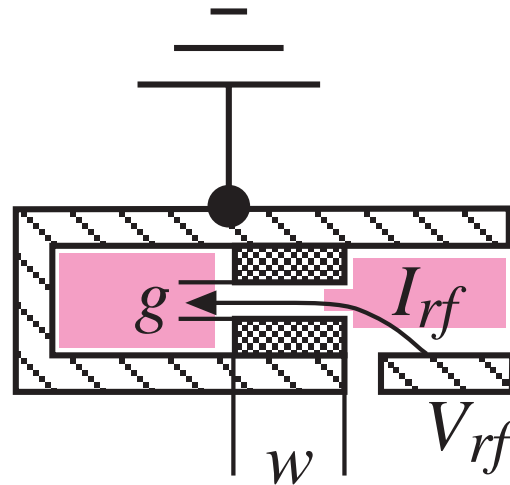
DISCHARGE MAINTENANCE IN SLOT AND PERIPHERY

DISCHARGE IN SLOT



- What are conditions for discharge maintained in slot?
(“Maintenance curve”)
- “Breakdown” in slot not an issue with main discharge present
- Discharge in slot \implies discharge in periphery

DISCHARGE IN PERIPHERY



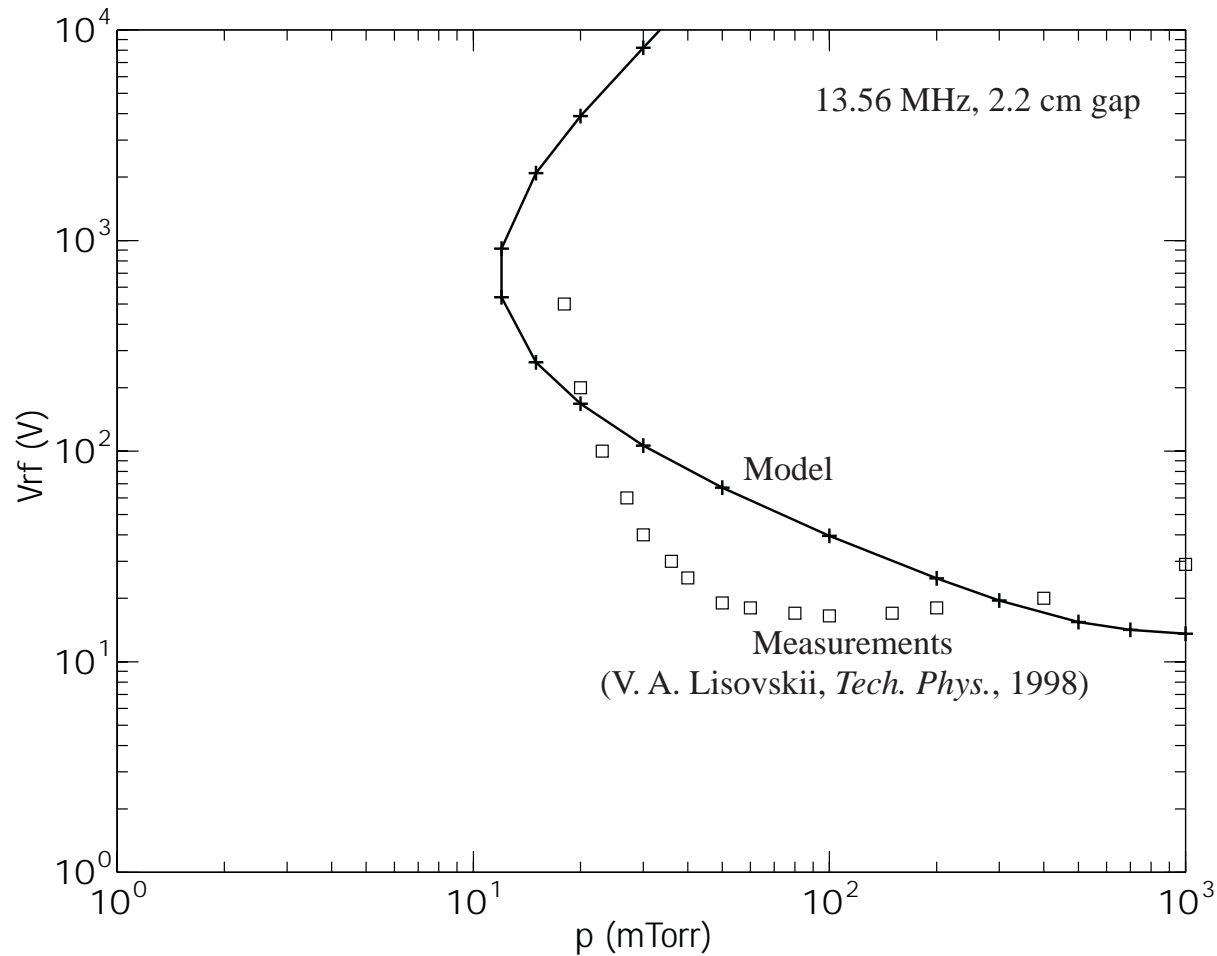
- For no discharge in slot, what are conditions for discharge maintained in periphery?
- “Breakdown” of periphery (as opposed to maintenance) may be an issue (to be investigated)
- Discharge in periphery $\not\Rightarrow$ discharge in slot

1D MODEL OF DISCHARGE MAINTENANCE

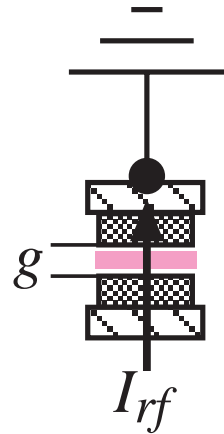
- Basic physics:
 - At low voltages (densities), total width of sheaths approaches gap spacing \Rightarrow bulk plasma becomes too thin
 - Ionization balance or power balance is lost
- Global model with additional physics at low rf voltages:
 - Account for a dc/low frequency sheath width in the absence of a high frequency sheath (Godyak/Sternberg, 1990)
 - Account for high frequency voltage drops across the dc/low frequency sheaths and the bulk plasma
 - Account for transition from ambipolar to free diffusion as bulk plasma becomes thin (Allis/Rose 1954)

BENCHMARK 1D MODEL AGAINST MEASUREMENTS

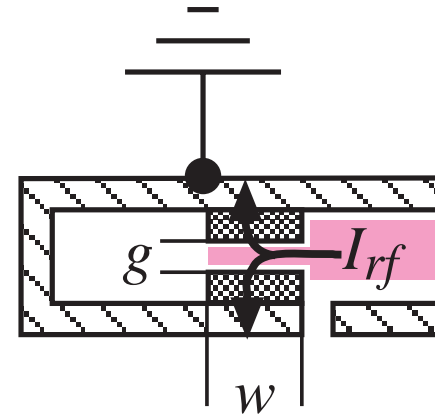
- Conventional capacitive discharge (argon)



2D RF CURRENT FLOWS IN SLOT



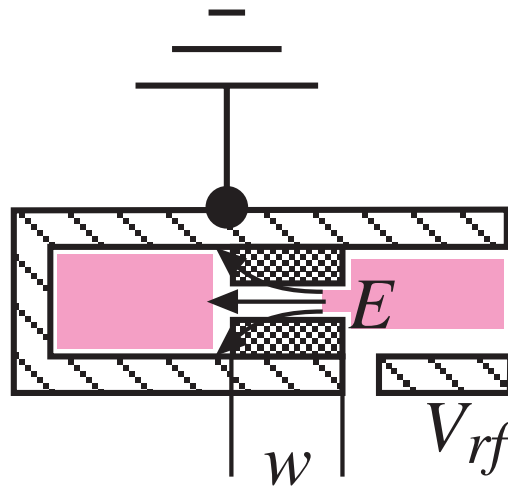
Conventional
rf discharge



Slot discharge

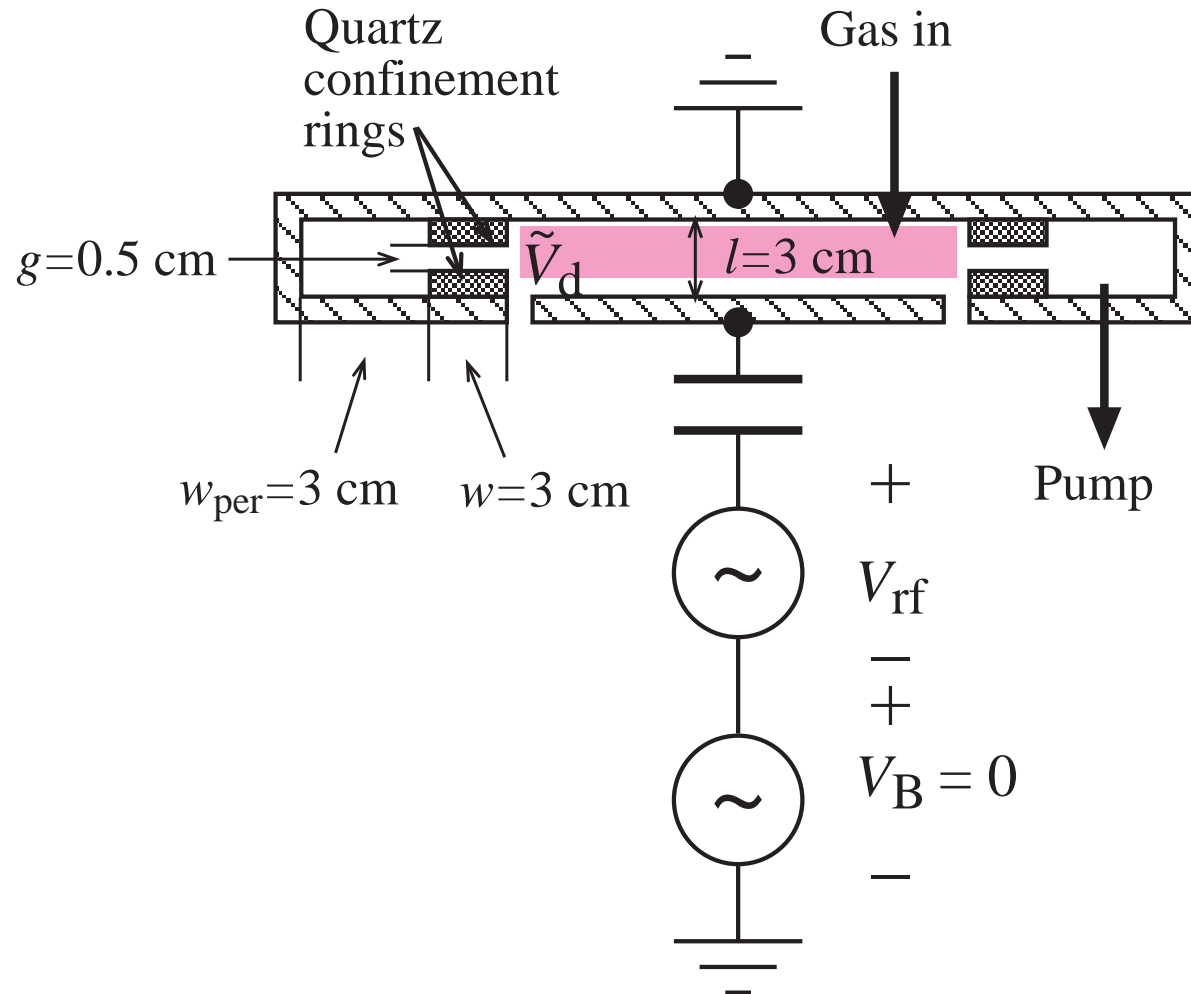
- Standard 1D global model has rf current transverse to plates
- Symmetric excitation of discharge in slot has 2D currents
⇒ enhanced ohmic heating, incorporated into model
- When periphery ignites, current drawn through slot increases
⇒ incorporated into model

2D CAPACITIVE COUPLING ACROSS SLOT



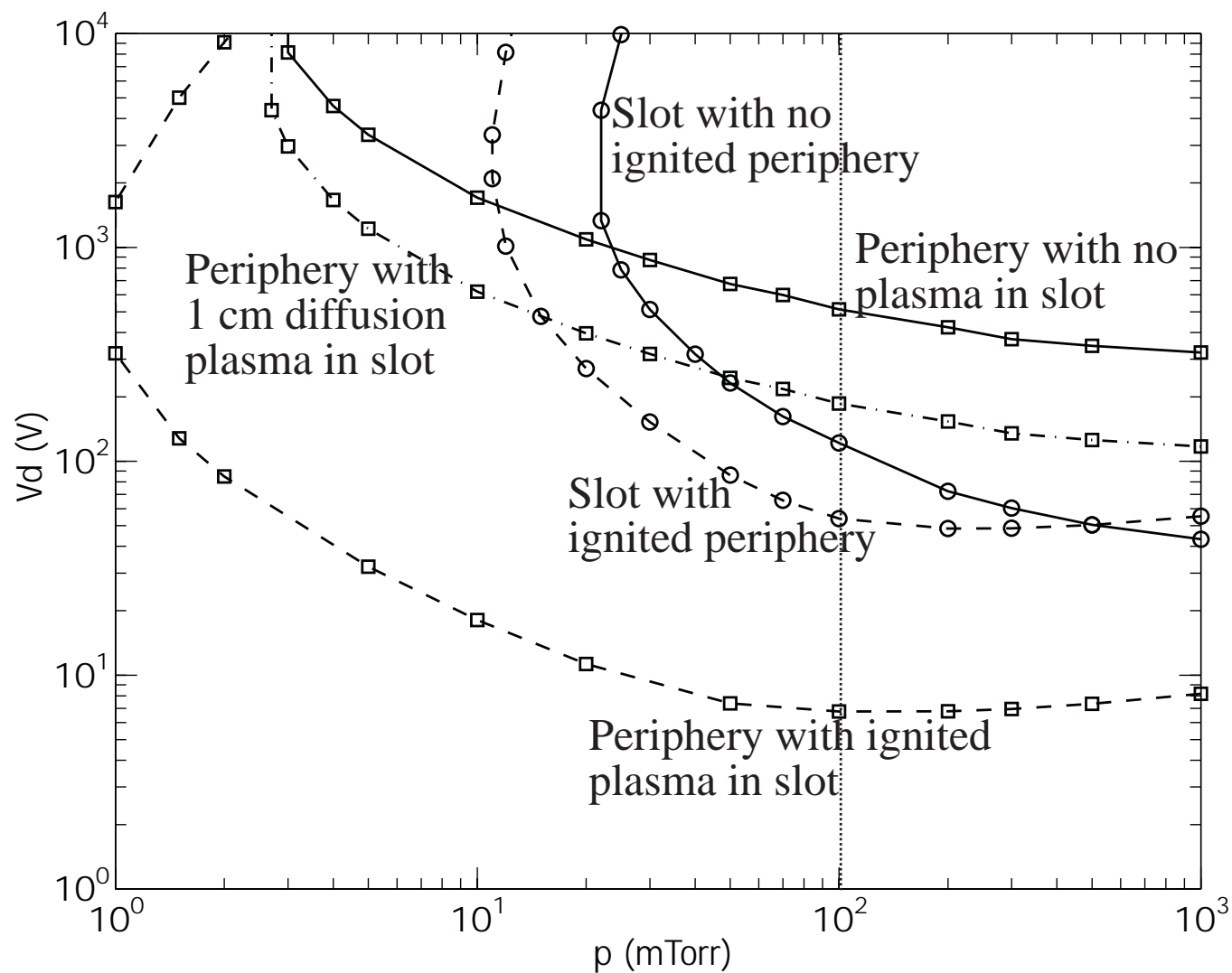
- Solve for decay of electric field E in dielectric region
- Decay depends on pinch-off length
⇒ incorporated into model

NOMINAL PARAMETERS



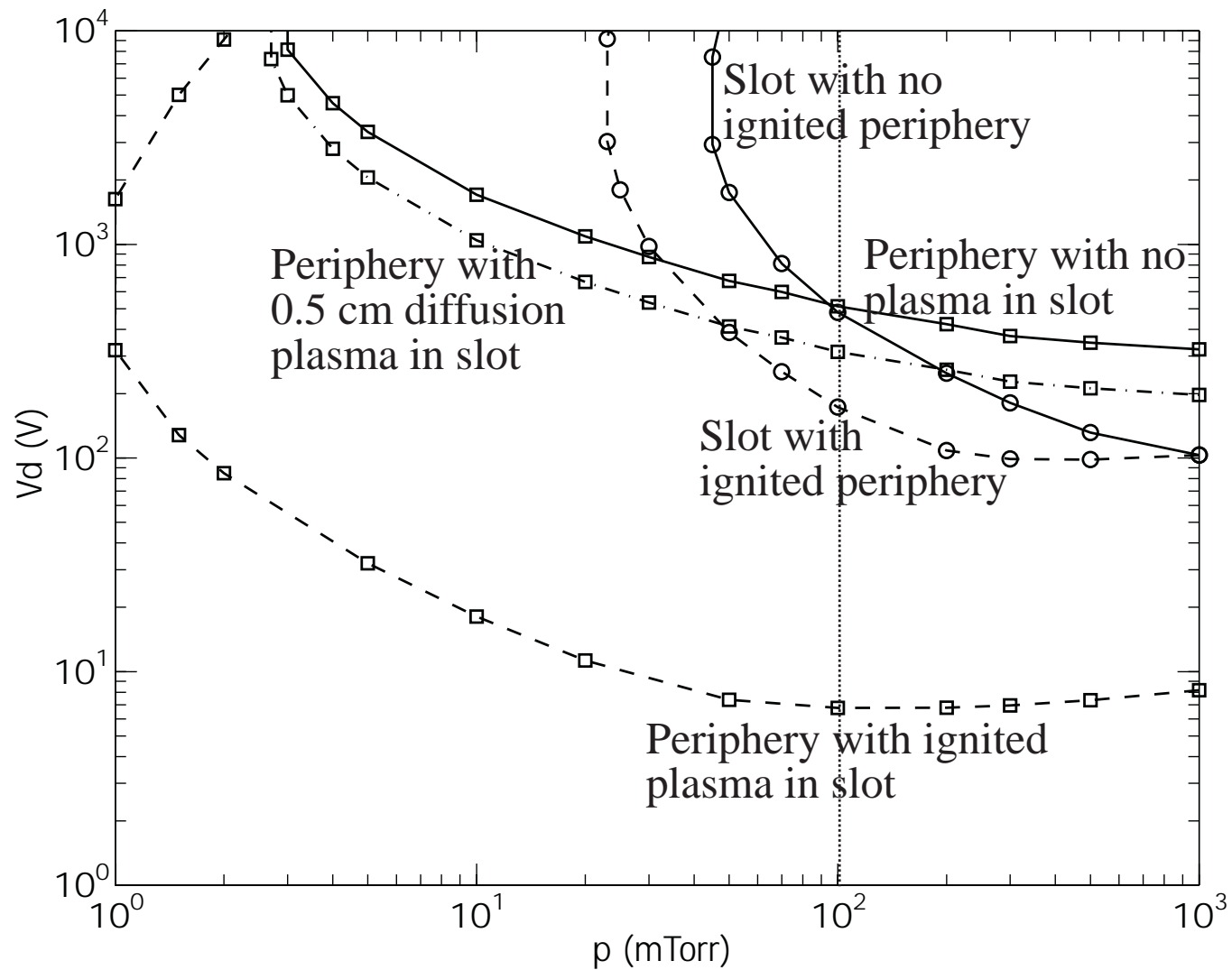
- Plot \tilde{V}_d versus pressure for maintenance in slot and periphery

MAINTENANCE FOR NOMINAL PARAMETERS



- At 100 mTorr, slot ignites, then periphery ignites

HALVE GAP SIZE TO 0.25 CM



- Now at 100 mTorr, periphery ignites, then slot ignites

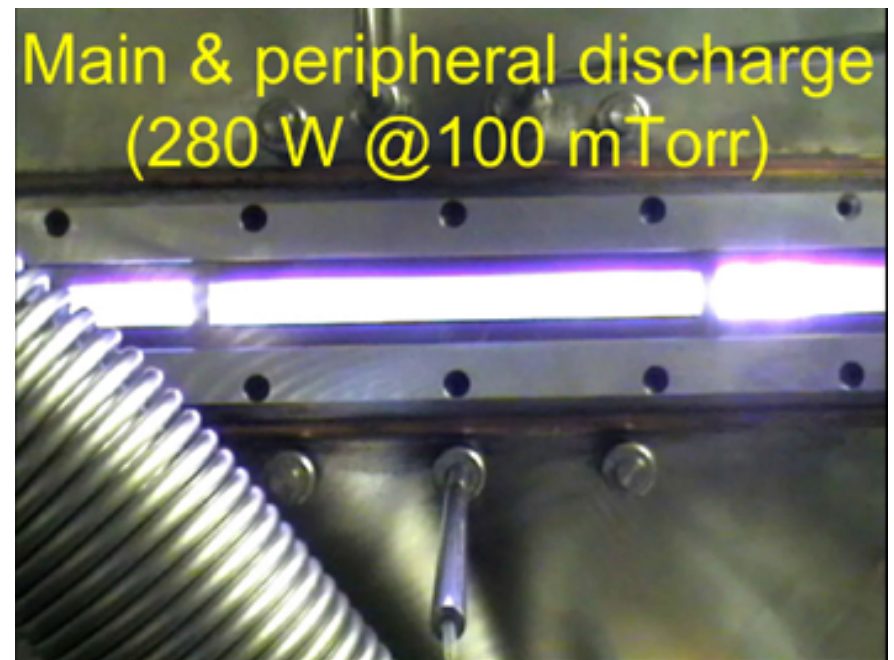
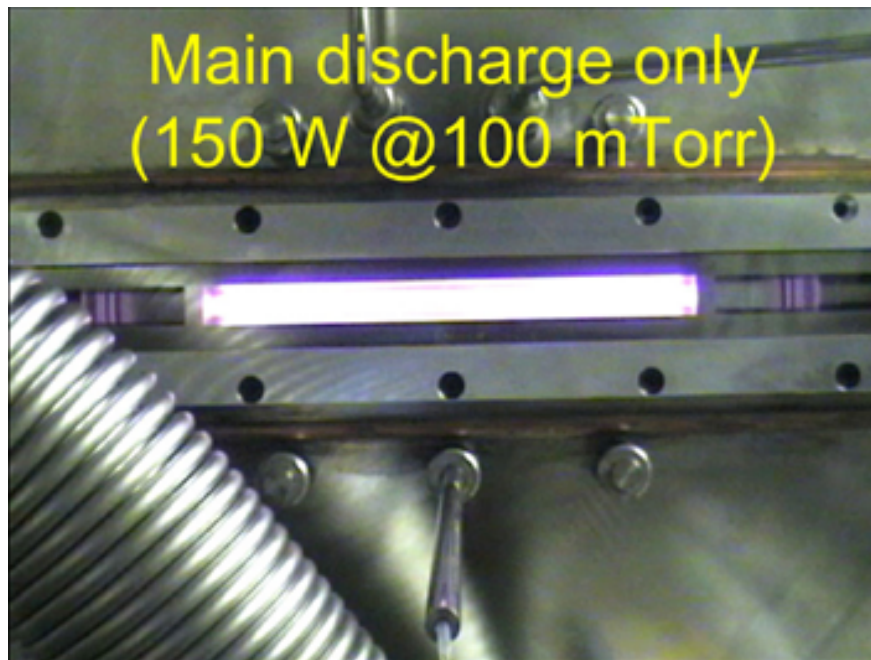
BERKELEY EXPERIMENT

Sungjin Kim
J.T. Gudmundsson
Sangsup Jeong

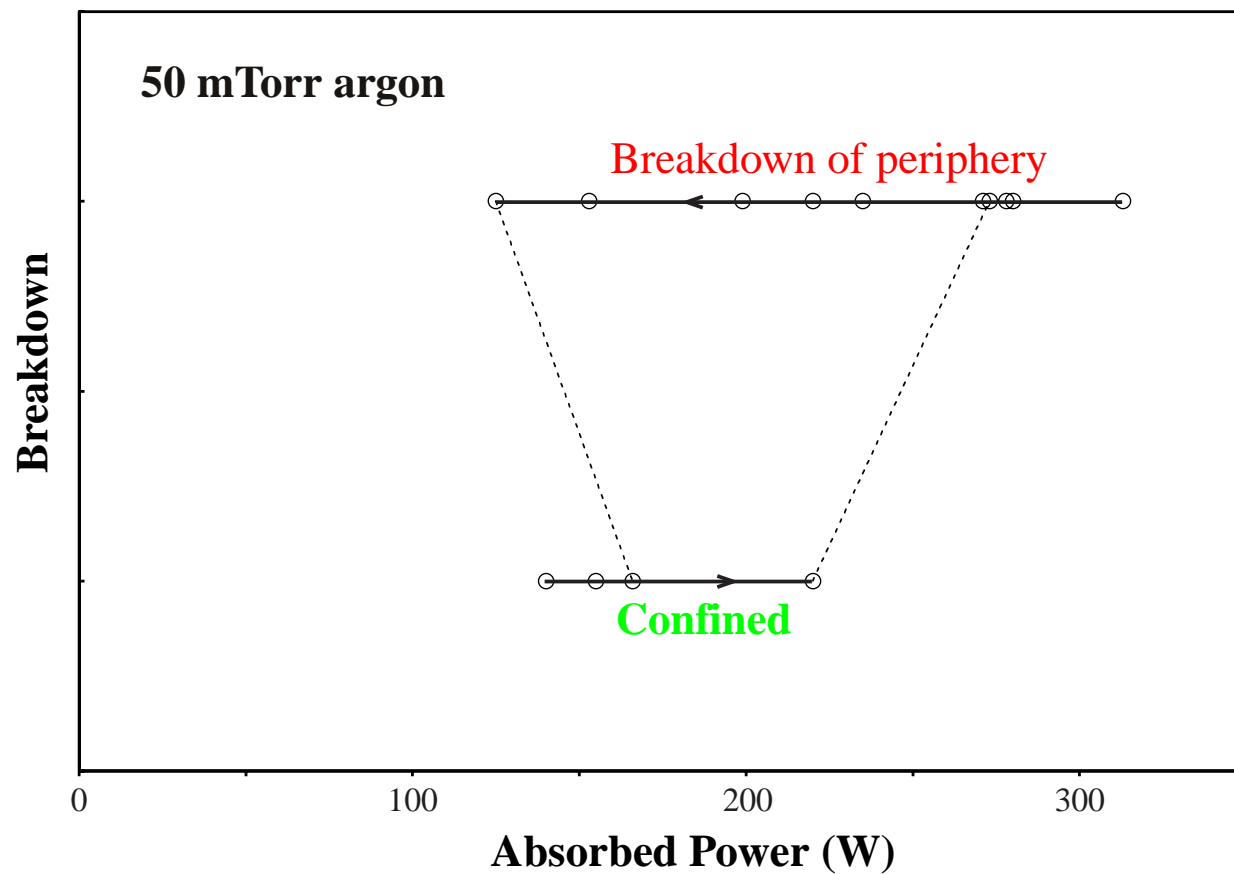
CONFINED AND UNCONFINED PLASMA

- 27 MHz, 5 '' diameter powered electrode, 1/4'' slot gap g

(View through window along a diameter of the grounded electrode)

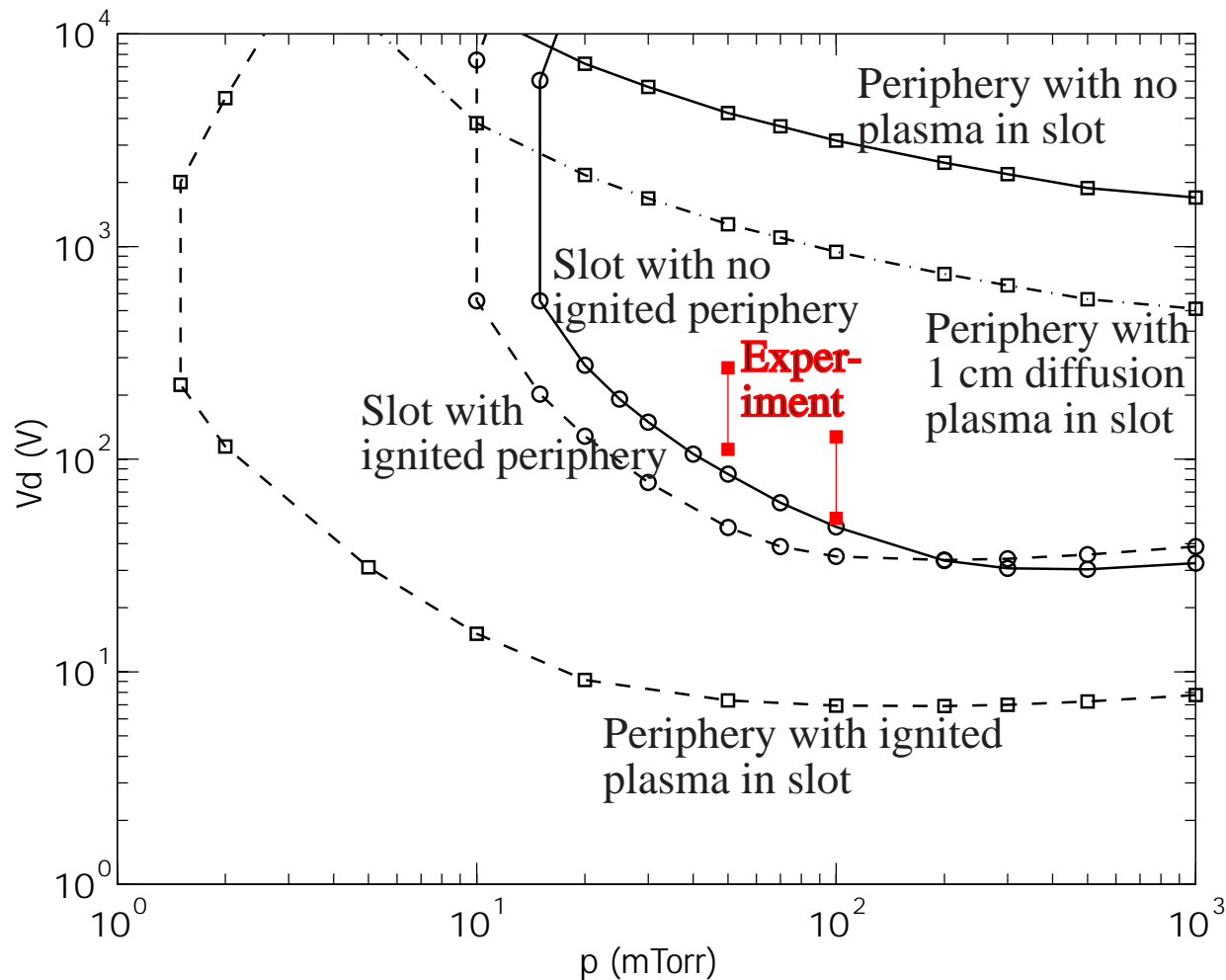


HYSTERESIS IN POWER CHARACTERISTICS



MAINTENANCE IN BERKELEY EXPERIMENT

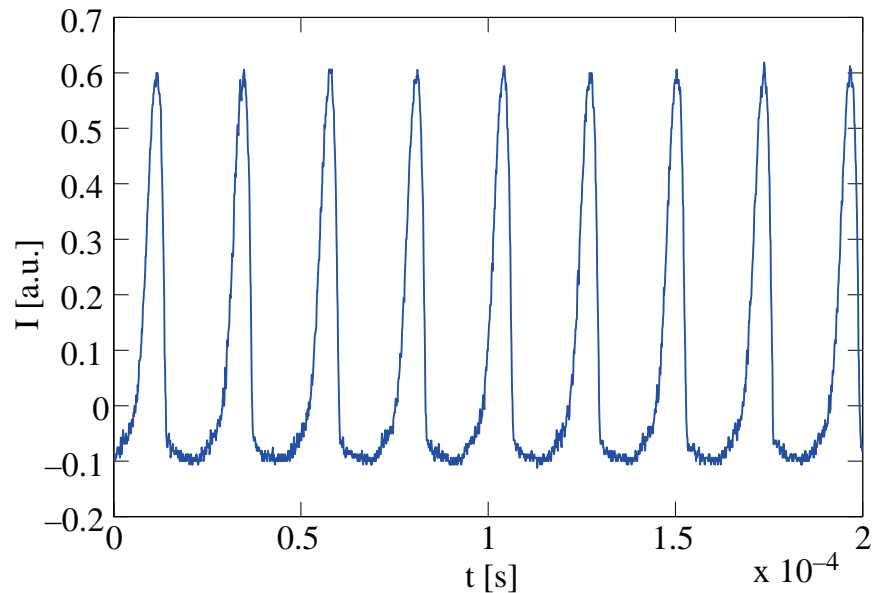
- $l = 2.54$ cm, $g = 0.635$ cm, $w = 3.8$ cm, $w_{\text{per}} = 5.1$ cm



INSTABILITIES WITH PERIPHERAL PLASMA

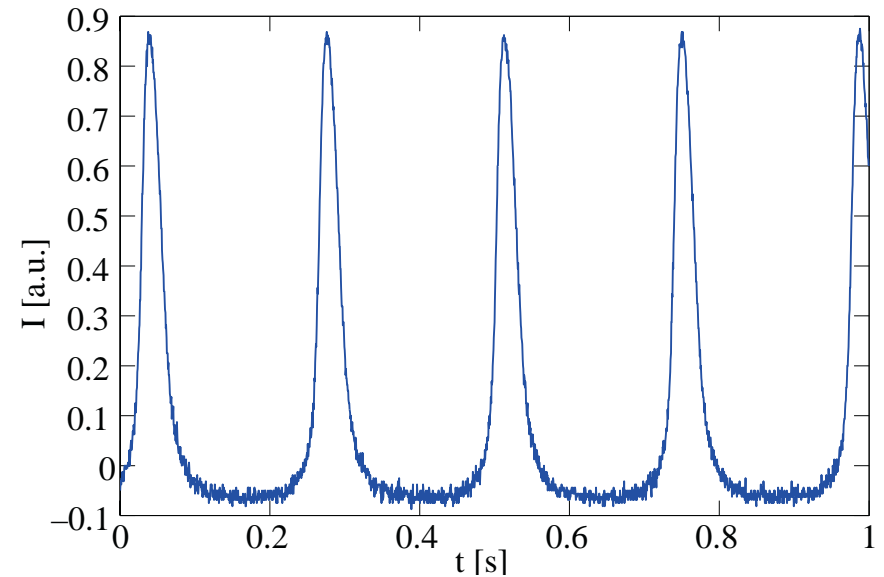
- 748.7 nm argon optical emission line in main discharge
(the zero of I is not calibrated)

80 W, 100 mTorr



High frequency (43.3 kHz)
relaxation oscillation

202 W, 77 mTorr



Low frequency (4.2 Hz)
relaxation oscillation

FUTURE PLANS

- Measure the rf voltage on main discharge plasma
- Experimentally characterize single frequency ignition (27 MHz) as a function of voltage, pressure, and gap spacing
- Experimentally characterize dual frequency ignition (27/2 MHz)
- Experimentally characterize instabilities and develop theoretical model
- Model effect of aspect-ratio of periphery on maintenance
- Model the effect of transport of electrons past pinch-off on peripheral ignition
- Model “breakdown” of periphery for no plasma in slot